

3. (Amended) The fabrication method of a semiconductor device according to claim [2] 8,  
wherein said step of planarization comprises the step of effecting planarization by polishing said first  
and second insulation films.

4. (Amended) The fabrication method of a semiconductor device according to claim [2] 8,  
wherein said second insulation film includes a silicon oxide film formed by plasma CVD.

5. (Amended) [The] A fabrication method of a semiconductor device [according to claim  
2] comprising the steps of:

forming a first insulation film on a substrate,

forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after  
forming said second insulation film, and

effecting planarization by polishing at least said second insulation film,

wherein said step of introducing impurities comprises the steps of

forming a photoresist on a surface of a device before impurities are introduced to said first  
insulation film, and

introducing impurities into said first insulation film via said photoresist film.

6. (Amended) [The] A fabrication method of a semiconductor device [according to claim  
2] further comprising the step of] comprising the steps of:

forming a first insulation film on a substrate,

forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after  
forming said second insulation film.

effecting planarization by polishing at least said second insulation film, and

forming a third insulation film on a surface of a device after said first polishing.

7. (Amended) [The] A fabrication method of a semiconductor device [according to claim 2, further comprising the step of] comprising the steps of:

forming a first insulation film on a substrate,

forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after

forming said second insulation film,

effecting planarization by polishing at least said second insulation film, and

forming a fourth insulation film on a surface of a device before said first insulation film is formed.

8. (Amended) [The] A fabrication method of a semiconductor device [according to claim 2] comprising the steps of:

forming a first insulation film on a substrate,

forming a second insulation film on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after

forming said second insulation film, and

effecting planarization by polishing at least said second insulation film,

wherein said insulation film includes a silicon dioxide material containing at least 1% of carbon.

9. (Amended) The fabrication method of a semiconductor device according to claim [2] 8, wherein said first insulation film includes a material having a contact angle of purified water of not more than 30° [of purified water] with respect to said first insulation film.

10. (Amended) The fabrication method of a semiconductor device according to claim [2] 8, wherein said first insulation film includes an inorganic SOG film.

*Subj*

11. (Amended) The fabrication method of a semiconductor device according to claim [2] 8, wherein said polishing is carried out by chemical mechanical polishing.

*B2  
B3  
B4  
B5*

13. (Amended) The fabrication method of a semiconductor device according to claim [2] 8, wherein said step of introducing impurities comprises the step of introducing impurities into said first insulation film by implantation.

*C13*

16. (Amended) The fabrication method of a semiconductor device according to claim [15] C, wherein said step of introducing impurities comprises the step of introducing impurities only to a surface of said first insulation film.

*B3  
Subj*

17. (Amended) [The] A fabrication method of a semiconductor device [according to claim 15] comprising the steps of:  
forming a first insulation film on a substrate,  
introducing impurities at least to a surface of said first insulation film,  
effecting planarization by polishing said first insulation film, and  
forming a third insulation film on a surface of a device after said polishing.

18. (Amended) [The] A fabrication method of a semiconductor device [according to claim 15] comprising the steps of:  
forming a first insulation film on a substrate,  
introducing impurities at least to a surface of said first insulation film, and  
effecting planarization by polishing said first insulation film, and  
forming a fourth insulation film on a surface of a device before said first insulation film is formed.

19. (Amended) [The] A fabrication method of a semiconductor device [according to claim 15] comprising the steps of:

forming a first insulation film on a substrate,

introducing impurities at least to a surface of said first insulation film, and

effecting planarization by polishing said first insulation film,

wherein said first insulation film includes a silicon oxide material containing at least 1% of carbon.

17. (Amended) The fabrication method of a semiconductor device according to claim [15]

18. wherein said first insulation film includes a material having a contact angle of purified water of not more than 30° [of purified water] with respect to said first insulation film.

19. (Amended) The fabrication method of a semiconductor device according to claim [15]

20. wherein said first insulation film includes an inorganic SOG film.

21. (Amended) The fabrication method of a semiconductor device according to claim [15]

22. wherein said polishing is carried out by chemical mechanical polishing.

23. (Amended) The fabrication method of a semiconductor device according to claim [15]

24. wherein a surfactant is used in said polishing step.

25. (Amended) The fabrication method of a semiconductor device according to claim [15]

26. wherein said step of introducing impurities comprises the step of introducing impurities into said first insulation film by implantation.

27. (Amended) The fabrication method of a semiconductor device according to claim [15]

28. wherein said impurities include at least one element selected from the group consisting of argon, boron, nitrogen and phosphorus.

29. (Amended) [The] A fabrication method of a semiconductor device comprising the steps

of:

30. forming a first insulation film on a substrate,

31. forming a second insulation film on said first insulation film,[and]